



Bipolar NPN Bare Die – BTN6013

Part Description

The BTN6013 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = 60V
- VCEO = 60V
- VEBO = 7V
- hFE = 200-400 @ VCE = 1V, IC = 2A
- VCE(Sat) = 0.3V @ IC = 2A, IB = 200mA
- fT = 70 MHz @ VCE = 10V, IE = 0A
- COBO = 70pF @ VCB = 10V

Features

Very Low VCE(sat). Designed to provide performance equivalent to KEC KTD1691

Die Size (Unawn)

2000µm X 2000µm, 79 Mils X 79 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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